

SI2323DDS-T1-GE3

SI2323DDS-T1-GE3 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



SI2323DDS-T1-GE3 Specifications

Manufacturer Part Number	SI2323DDS-T1-GE3
Manufacturer	Vishay Siliconix
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-236-3, SC-59, SOT-23-3
Series	TrenchFET?
FET Type	P-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	20V
Current - Continuous Drain (Id) @ 25°C	5.3A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs(th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	36nC @ 8V
Input Capacitance (Ciss) (Max) @ Vds	1160pF @ 10V
Vgs (Max)	$\pm 8V$
FET Feature	-
Power Dissipation (Max)	960mW (Ta), 1.7W (Tc)
Rds On (Max) @ Id, Vgs	39 mOhm @ 4.1A, 4.5V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Supplier Device Package	SOT-23
Package / Case	TO-236-3, SC-59, SOT-23-3
	Report errors?

SI2323DDS-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

SI2323DDS-T1-GE3 Payment Methods





If you have any question about SI2323DDS-T1-GE3, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com